

## Silicon PNP Power Transistors

## 2SB755

## DESCRIPTION

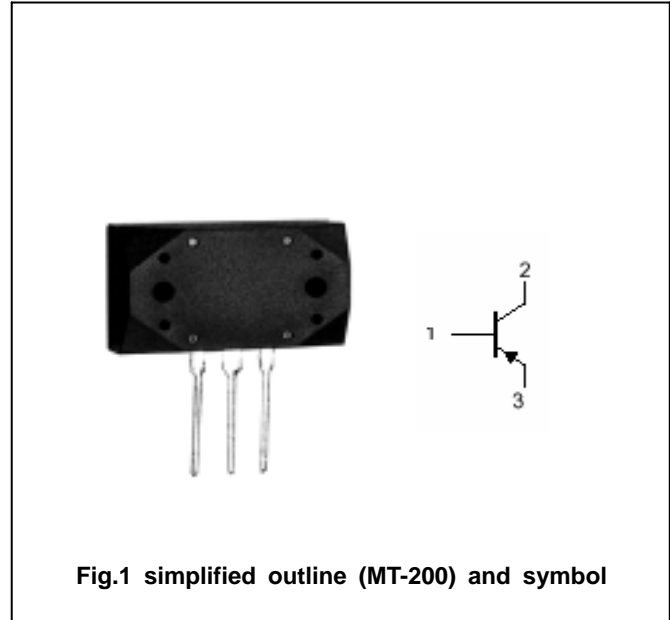
- With MT-200 package
- Complement to type 2SD845
- High transition frequency
- High breakdown voltage : $V_{CEO}=-150V(\text{min})$

## APPLICATIONS

- For power amplifier applications

## PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings ( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-150	V
$V_{CEO}$	Collector-emitter voltage	Open base	-150	V
$V_{EBO}$	Emitter-base voltage	Open collector	-5	V
$I_C$	Collector current		-12	A
$I_B$	Base current		-1.2	A
$P_C$	Collector power dissipation	$T_C=25$	120	W
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-55~150	

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-0.1A; I <sub>B</sub> =0	-150			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =-10mA; I <sub>C</sub> =0	-5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-5 A; I <sub>B</sub> =-0.5 A			-2.0	V
V <sub>BE</sub>	Base-emitter on voltage	I <sub>C</sub> =-5A ; V <sub>CE</sub> =-5V			-1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-150V; I <sub>E</sub> =0			-50	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-5V; I <sub>C</sub> =0			-50	μ A
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =-1A ; V <sub>CE</sub> =-5V	55		160	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-1A ; V <sub>CE</sub> =-10V		20		MHz
C <sub>OB</sub>	Output capacitance	I <sub>E</sub> =0; V <sub>CB</sub> =-10V;f=1MHz		450		pF

◆ h<sub>FE</sub> classifications

R	O
55-110	80-160

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PACKAGE OUTLINE

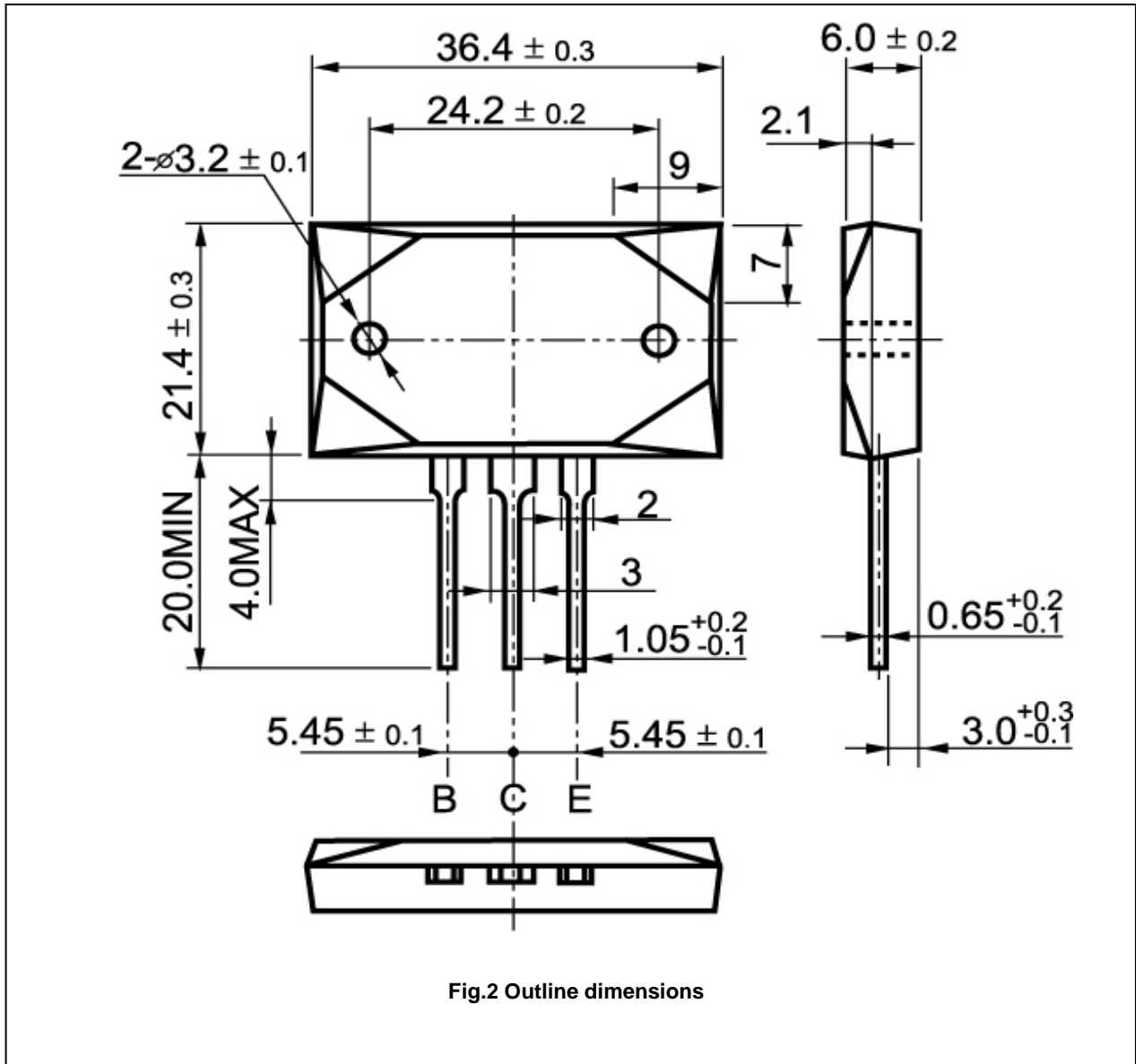


Fig.2 Outline dimensions